

**IN THE CLAIMS:**

Claims 1-22 (Cancel without prejudice or disclaimer)

23. (Currently Amended) A process for fabricating an integrated circuit, comprising:  
providing a doped substrate having a source, a drain and a channel extending from said  
source to said drain, wherein said source and said drain do not include a lightly doped regions;  
forming an oxide over said channel said oxide being defined by a width, wherein said  
oxide and said substrate form an interface that is substantially stress free and planar; and  
forming a gate structure over a substrate, said gate structure having a length of  
approximately 1.25  $\mu\text{m}$  or less and being coextensive with said width of said oxide; and  
~~forming a source and a drain, said source and said drain not having lightly doped regions.~~

24. (Currently Amended) A process ~~for fabricating an integrated circuit~~ as recited in  
claim 23, wherein said process further comprises forming a said channel before forming said  
source and said drain.

Kindly cancel Claim 25 without prejudice or disclaimer.

26. (Original) A process as recited in claim 24, wherein said channel is doped by a halo  
implantation.

27. (Original) A process as recited in claim 23, wherein said length is in the range of  
approximately 0.25  $\mu\text{m}$  to approximately 0.05  $\mu\text{m}$ .

28. (Currently Amended) A process as recited in claim ~~25~~ 23, wherein said oxide layer has a first oxide portion and a second oxide portion.

29. (Original) A process as recited in claim 23, wherein a spacer is not formed adjacent said gate structure.

30. (Currently Amended) A process as recited in claim ~~25~~ 23, wherein said oxide layer has a thickness in the range of approximately 1.5 nm to approximately 20.0 nm.

31. (Currently Amended) A process as recited in claim 23, wherein said source and said drain ~~having~~ have doping levels in the range of approximately  $1 \times 10^{20}/\text{cm}^3$  to  $5 \times 10^{20}/\text{cm}^3$ .

32. (Currently Amended) A process as recited in claim ~~24~~ 23, wherein said channel has a doping level in the range of approximately  $1 \times 10^{16}/\text{cm}^3$  to approximately  $1 \times 10^{19}/\text{cm}^3$ .

Kindly cancel Claims 33-40 without prejudice or disclaimer.